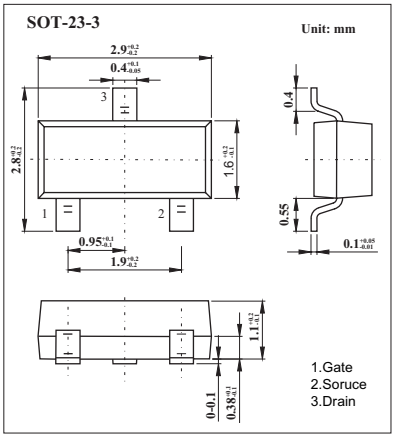
MTB080P06N3

P-Channel Enhancement Mode MOSFET

BV_{DSS}		-60V
I_D@V_{GS}=-10V, T_A=25°C		-3.0A
$R_{DSON(TYP)}$	V_{GS}=-10V, I_D=-3A	155mΩ
	V_{GS}=-4.5V, I_D=-2.7A	208mΩ



Absolute Maximum Ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-Source Voltage		V_{DS}	-60	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current @ V_{GS}=-10V	T_A=25°C	I_D	-3.0	A
	T_A=70°C		-2.5	
Pulsed Drain Current	(Note 1&2)	I_{DM}	-10	
Maximum Power Dissipation	T_A=25°C	P_D	1.25	W
	T_A=70°C		0.8	
Operating Junction and Storage Temperature		Tj, Tstg	-55~+150	°C

Electrical Characteristics (Tj=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV_{DSS}	-60	-	-	V	V_{GS}=0V, I_D=-250μA
$V_{GS(th)}$	-1.0	-	-2.5		V_{DS}=V_{GS}, I_D=-250μA
I_{GSS}	-	-	±100	nA	V_{GS}=±20V, V_{DS}=0V
I_{DSS}	-	-	-1	μA	V_{DS}=-48V, V_{GS}=0V
	-	-	-10		V_{DS}=-48V, V_{GS}=0V, Tj=55°C
*$R_{DS(ON)}$	-	155	204	mΩ	V_{GS}=-10V, I_D=-3A
	-	159	250		V_{GS}=-4.5V, I_D=-2.7A
*G_{FS}	-	5	-	S	V_{DS}=-10V, I_D=-2A
Dynamic					
Ciss	-	511	-	pF	V_{DS}=-25V, V_{GS}=0V, f=1MHz
Coss	-	57	-		
Crss	-	40	-		
*$t_{d(ON)}$	-	6.8	-	ns	V_{DS}=-30V, I_D=-2A, V_{GS}=-10V, R_G=3Ω
*t_r	-	18.2	-		
*$t_{d(OFF)}$	-	26.4	-		
*t_f	-	7.6	-		
*Qg	-	12	-	nC	V_{DS}=-48V, I_D=-2A, V_{GS}=-10V
*Qgs	-	1.7	-		
*Qgd	-	3	-		

■ Marking

Marking	B8P6